

TCO12RN



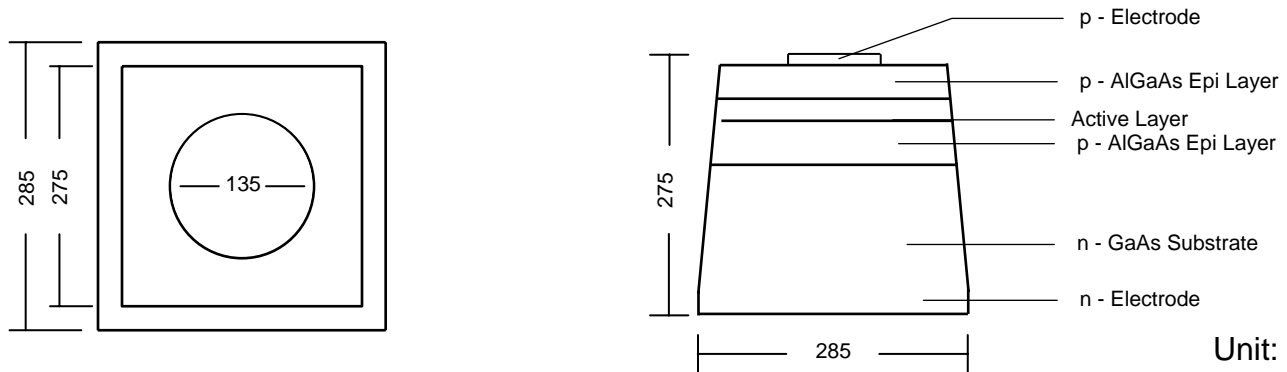
❖ Features:

- AlGaAs/GaAs Epi Wafer
- Double heterojunction structure

❖ Typical Applications:

- Lamp
- Display

❖ Outline Dimensions:



Unit: μm

❖ Physical Structure:

Chip dimensions		Chip size	11 mil x 11 mil	285 μm x 285 μm
		Thickness	11 mil	275 μm
		Emission area	11 mil	270 μm
		Bonding pad	5.3 mil	135 μm
Electrode	Top	P (anode)	Aluminium (Gold optional)	
	Backside	N (cathode)	Gold alloy	

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	-	1.85	2.00	V
Wavelength	λ_P	$I_F = 20\text{mA}$	-	660	-	nm
	Hue		-	640	-	
Spectral width at half height	$\Delta\lambda$	$I_F = 20\text{mA}$	-	20	-	nm
Reverse Current	I_R	$V_R = 5\text{V}$	-	-	10	μA
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5.0	-	-	V
Luminous Intensity	I_V	$I_F = 20\text{mA}$	15	-	-	mcd

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